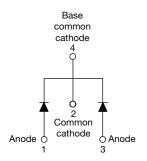


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HEXFRED® Ultrafast Soft Recovery Diode, 2 x 8 A





PRIMARY CHARACTERISTICS								
I _{F(AV)}	2 x 8 A							
V _R	600 V							
V _F at I _F	1.4 V							
t _{rr} typ.	18 ns							
T _J max.	150 °C							
Package	TO-220AB 3L							
Circuit configuration	Common cathode							

FEATURES

- · Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA16TA60C... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A per leg continuous current, the VS-HFA16TA60C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TA60C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V_{R}		600	V					
Maximum continuous forward current per leg		T _C = 100 °C	8						
per device	- I _F	1C = 100 C	16						
Single pulse forward current	I _{FSM}		60	A					
Maximum repetitive forward current	I _{FRM}		24						
Mayimum nauga discination	Б	T _C = 25 °C	36	W					
Maximum power dissipation	P_{D}	T _C = 100 °C	14	l vv					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					

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ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA	600	-	-				
Maximum forward voltage	V _{FM}	I _F = 8 A		ı	1.4	1.7	V		
		I _F = 16 A	See fig. 1	-	1.7	2.1			
		I _F = 8 A, T _J = 125 °C		-	1.4	1.7			
Maximum reverse	1	$V_R = V_R$ rated	See fig. 2	-	0.3	5.0	- μΑ		
leakage current	I _{RM}	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$	See lig. 2	-	100	500			
Junction capacitance	C _T	$V_R = 200 \text{ V}$ See fig. 3		-	10	25	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	8.0	-	nΗ		

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS				UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	A/μs, V _R = 30 V	-	18	-	ns		
Reverse recovery time See fig. 5 and fig. 10	t _{rr1}	T _J = 25 °C		-	37	55			
	t _{rr2}	T _J = 125 °C	$I_F = 8.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	55	90			
Peak recovery current	I _{RRM1}	$T_J = 25 ^{\circ}C$		-	3.5	5.0	- A - nC		
See fig. 6	I _{RRM2}	T _J = 125 °C		-	4.5	8.0			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	65	138			
See fig. 7	Q _{rr2}	T _J = 125 °C		-	124	360			
Peak rate of fall recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	240	-	A/µs		
	dI _{(rec)M} /dt2	T _J = 125 °C		-	210	-			

THERMAL - MECHANICAL SPECIFICATIONS PER LEG										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Junction to case, single leg conducting	В		-	-	3.5					
Junction to case, both legs conducting	R _{thJC}		-	-	1.75	K/W				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	I IVVV				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-					
Weight			-	2.0	-	g				
vveignt			-	0.07	-	OZ.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style 3L TO-220AB	HFA16TA60C							

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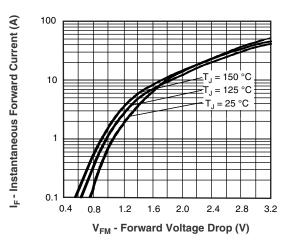


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

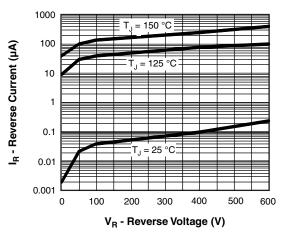


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

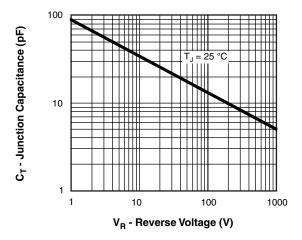


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

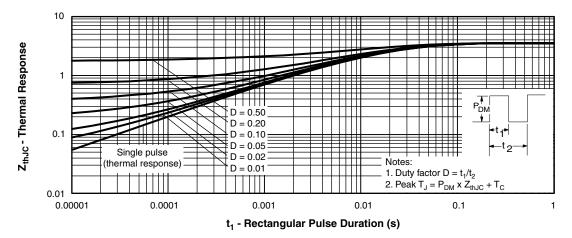


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

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 $V_R = 200 \text{ V}$

T_J = 125 °C

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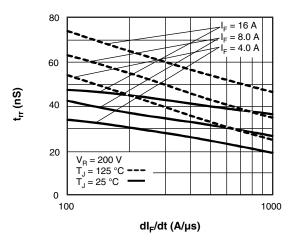
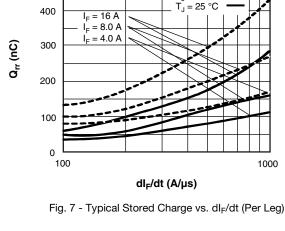


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)



500

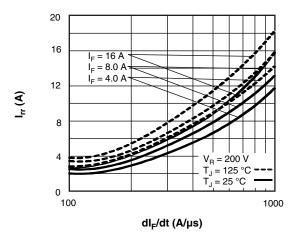


Fig. 6 - Typical Recovery Current vs. dI_F/dt (Per Leg)

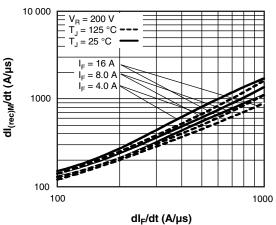
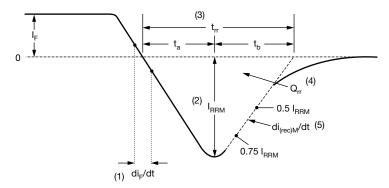


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. $dI_F/dt(Per Leg)$



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

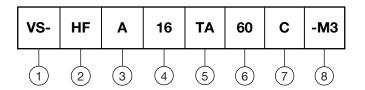
Fig. 9 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

- Current rating (16 = 16 A)

5 - Package:

TA = 3L TO-220AB

6 - Voltage rating (60 = 600 V)

7 - Circuit configuration:

C = common cathode

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

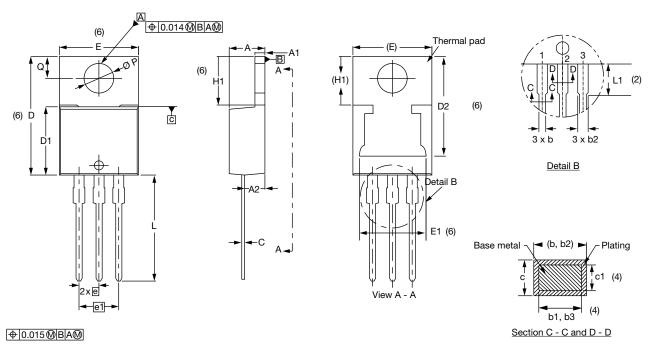
ORDERING INFORMATION (Example)								
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION						
VS-HFA16TA60C-M3	50	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96154					
Part marking information	www.vishay.com/doc?95028					
SPICE model	www.vishay.com/doc?96596					

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TO-220AB 3L

DIMENSIONS in millimeters and inches



Lead tip

Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355				•	•		•	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- 3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- $^{(7)}\,$ Outline conforms to JEDEC® TO-220, except D2

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